Inverter Grade Thyristors (Stud Version), 195 A

TO-209AB (TO-93)

FEATURES

- Center amplifying gate
- High surge current capability
- Low thermal impedance
- High speed performance
- Compression bonding
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

Pb-free

RoHS COMPLIANT

TYPICAL APPLICATIONS

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

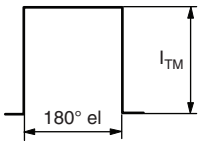
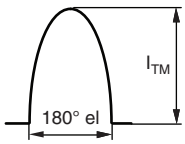
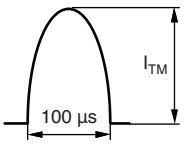
PRODUCT SUMMARY	
$I_{T(AV)}$	195 A
V_{DRM}/V_{RRM}	400 V, 800 V
V_{TM}	1.80 V
I_{TSM} at 50 Hz	4900 A
I_{TSM} at 60 Hz	5130 A
I_{GT}	200 mA
T_J	-40 °C to 125 °C
Package	TO-209AB (TO-93)
Diode variation	Single SCR

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		195	A
	T_C	85	°C
$I_{T(RMS)}$		306	A
I_{TSM}	50 Hz	4900	
	60 Hz	5130	
I^2t	50 Hz	120	kA^2s
	60 Hz	110	
V_{DRM}/V_{RRM}		400 to 800	V
t_q		15 to 20	µs
T_J		-40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM}, MAXIMUM REPETITIVE PEAK VOLTAGE V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST183S	04	400	500	40
	08	800	900	

CURRENT CARRYING CAPABILITY

FREQUENCY							UNITS
50 Hz	570	370	900	610	7040	5220	A
400 Hz	560	360	940	630	3200	2280	
1000 Hz	500	300	925	610	1780	1200	
2500 Hz	340	190	760	490	880	560	
Recovery voltage V_r	50		50		50		V
Voltage before turn-on V_d	V_{DRM}		V_{DRM}		V_{DRM}		
Rise of on-state current dI/dt	50		-		-		A/µs
Case temperature	60	85	60	85	60	85	°C
Equivalent values for RC circuit	47/0.22		47/0.22		47/0.22		Ω/µF

ON-STATE CONDUCTION

PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave			195	A
					85	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 74 °C case temperature			306	A
Maximum peak, one half cycle, non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	4900	
		t = 8.3 ms			5130	
		t = 10 ms	100 % V_{RRM} reapplied		4120	
		t = 8.3 ms			4310	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		120	kA^2s
		t = 8.3 ms			110	
		t = 10 ms	100 % V_{RRM} reapplied		85	
		t = 8.3 ms			78	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			1200	$kA^2\sqrt{s}$
Maximum peak on-state voltage	V_{TM}	I_{TM} = 600 A, $T_J = T_J$ maximum, t_p = 10 ms sine wave pulse			1.80	V
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			1.40	
High level value of threshold voltage	$V_{T(TO)2}$	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			1.45	
Low level value of forward slope resistance	r_{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.67	mΩ
High level value of forward slope resistance	r_{t2}	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.58	
Maximum holding current	I_H	T_J = 25 °C, I_T > 30 A			600	mA
Typical latching current	I_L	T_J = 25 °C, V_A = 12 V, R_a = 6 Ω, I_G = 1 A			1000	

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current		dI/dt	$T_J = T_J$ maximum, V_{DRM} = Rated V_{DRM} I_{TM} = 2 x dI/dt	1000	A/µs
Typical delay time		t_d	T_J = 25 °C, V_{DM} = Rated V_{DRM}, I_{TM} = 50 A DC, t_p = 1 µs Resistive load, gate pulse: 10 V, 5 Ω source	1.1	µs
Maximum turn-off time	minimum	t_q	$T_J = T_J$ maximum, I_{TM} = 300 A, commutating dI/dt = 20 A/µs V_R = 50 V, t_p = 500 µs, dV/dt: 200 V/µs	15	
	maximum			20	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V_{DRM}, higher value available on request	500	V/µs
Maximum peak reverse and off-state leakage current	I_{RRM}, I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	40	mA

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, f = 50 Hz, d% = 50	60	W
Maximum average gate power	$P_{G(AV)}$		10	
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq$ 5 ms	10	A
Maximum peak positive gate voltage	+ V_{GM}		20	V
Maximum peak negative gate voltage	- V_{GM}		5	
Maximum DC gate currrent required to trigger	I_{GT}	$T_J = T_J$ maximum V_A = 12 V, R_a = 6 Ω	200	mA
Maximum DC gate voltage required to trigger	V_{GT}		3	V
Maximum DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum, rated V_{DRM} applied	20	mA
Maximum DC gate voltage not to trigger	V_{GD}		0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	T_J		-40 to 125	°C
Maximum storage temperature range	T_{Stg}		-40 to 150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	0.105	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased	0.04	
Mounting torque, ± 10 %		Non-lubricated threads	31 (275)	N · m (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-209AB (TO-93)	

ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.016	0.012	$T_J = T_J$ maximum	K/W
120°	0.019	0.020		
90°	0.025	0.027		
60°	0.036	0.037		
30°	0.060	0.060		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

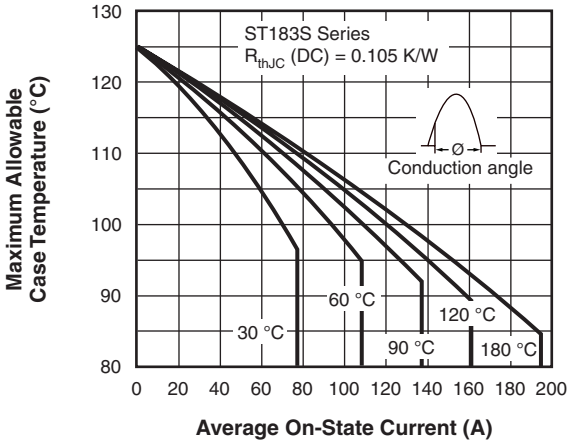


Fig. 1 - Current Ratings Characteristics

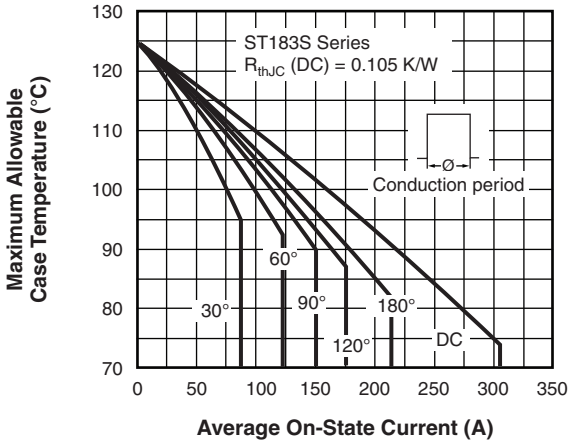
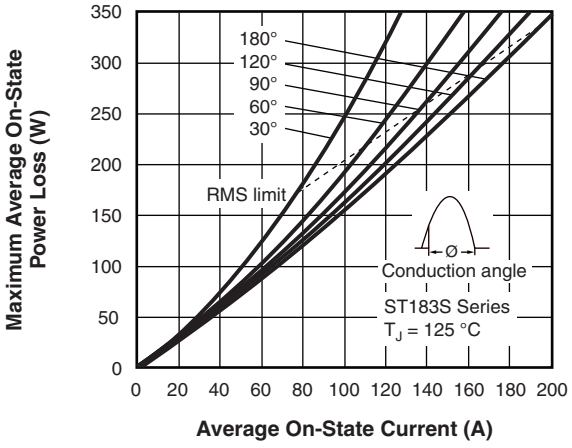


Fig. 2 - Current Ratings Characteristics



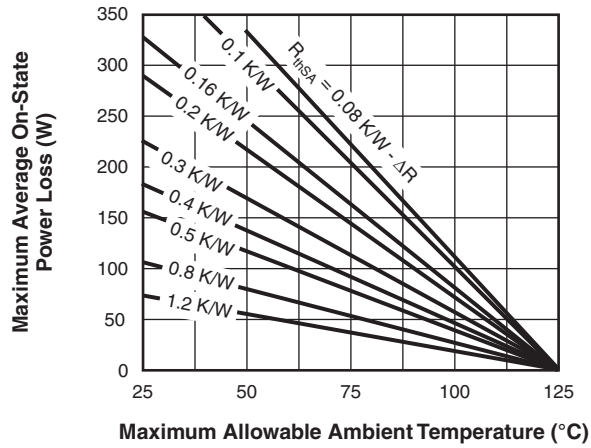
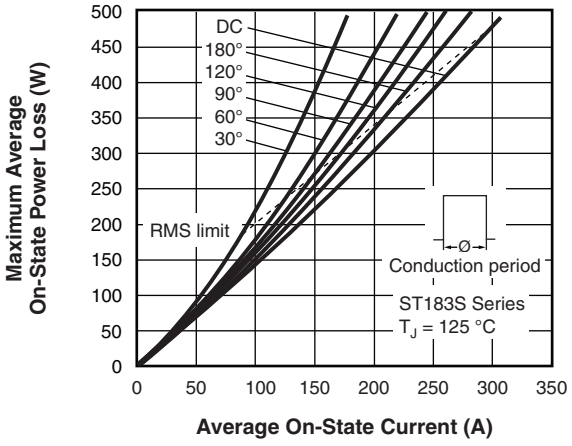


Fig. 3 - On-State Power Loss Characteristics



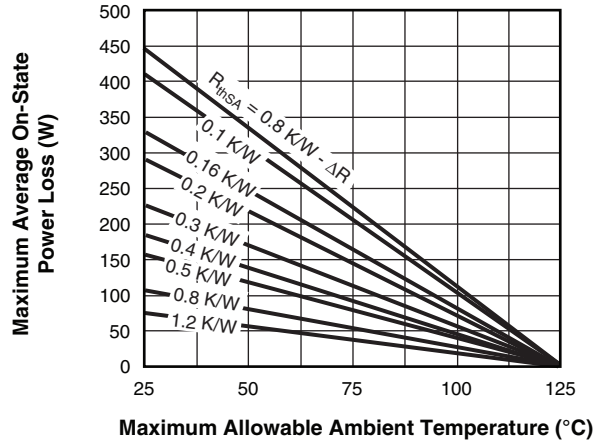


Fig. 4 - On-State Power Loss Characteristics

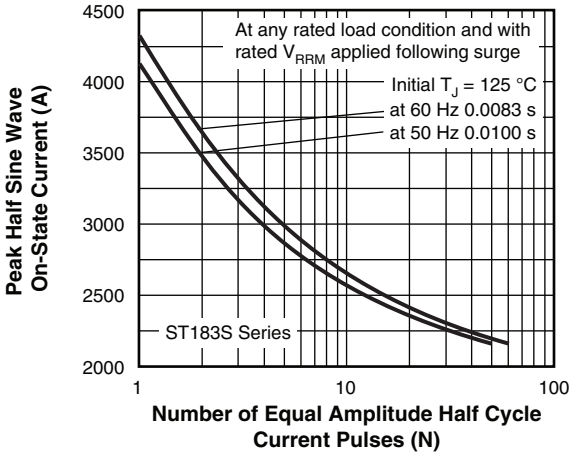


Fig. 5 - Maximum Non-Repetitive Surge Current

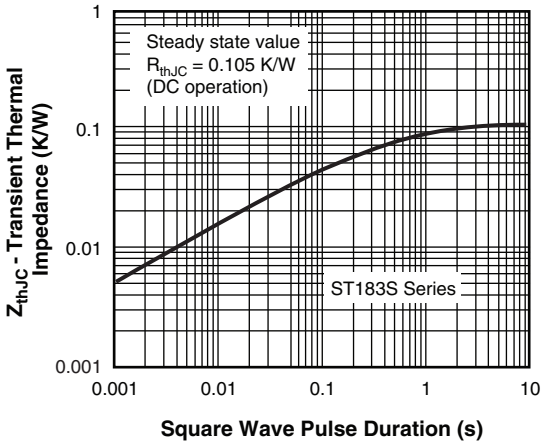


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

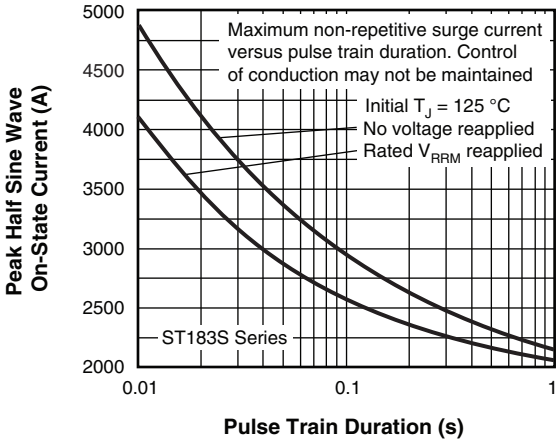


Fig. 6 - Maximum Non-Repetitive Surge Current

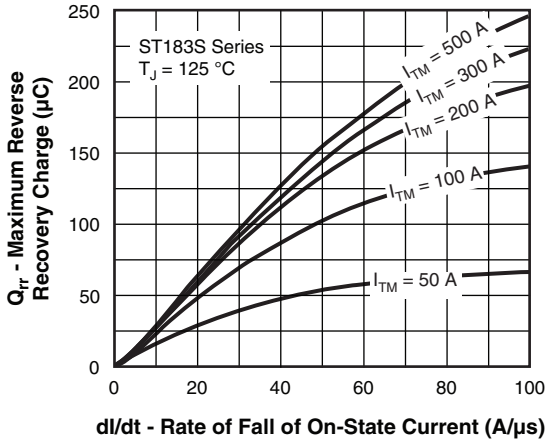


Fig. 9 - Reverse Recovered Charge Characteristics

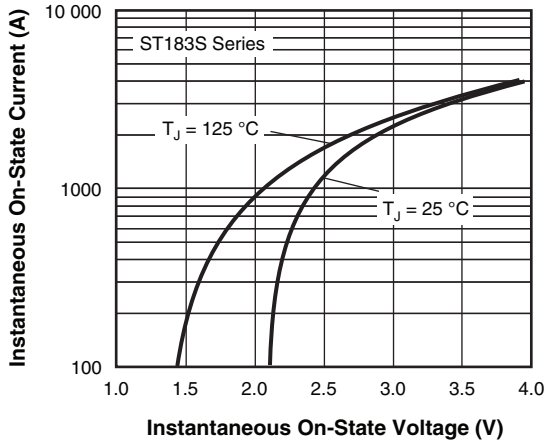


Fig. 7 - On-State Voltage Drop Characteristics

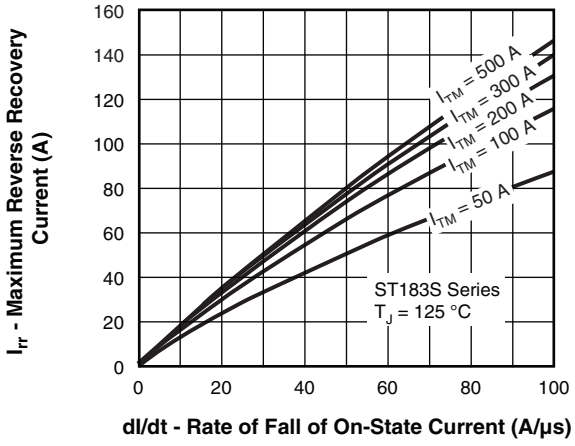


Fig. 10 - Reverse Recovery Current Characteristics

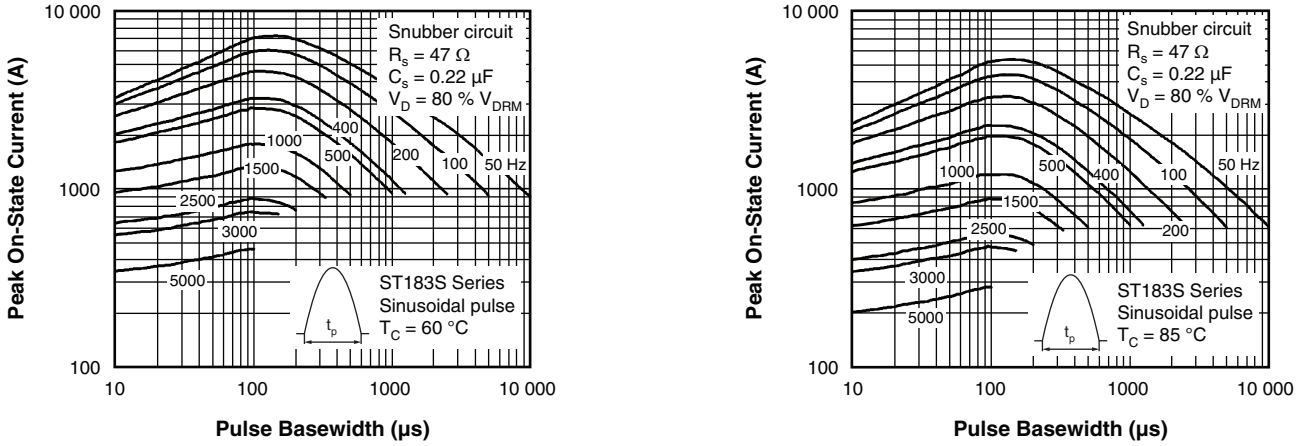


Fig. 11 - Frequency Characteristics

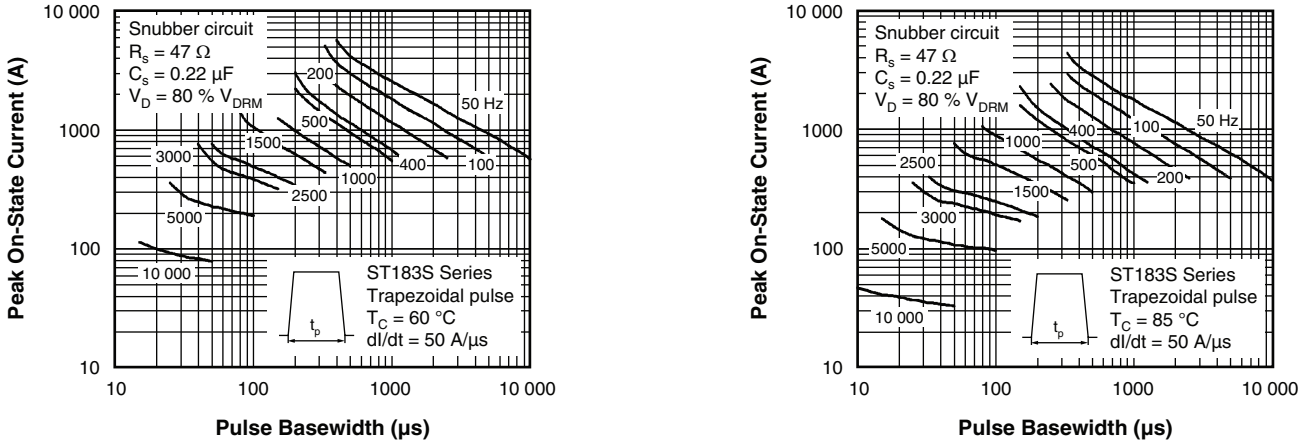


Fig. 12 - Frequency Characteristics

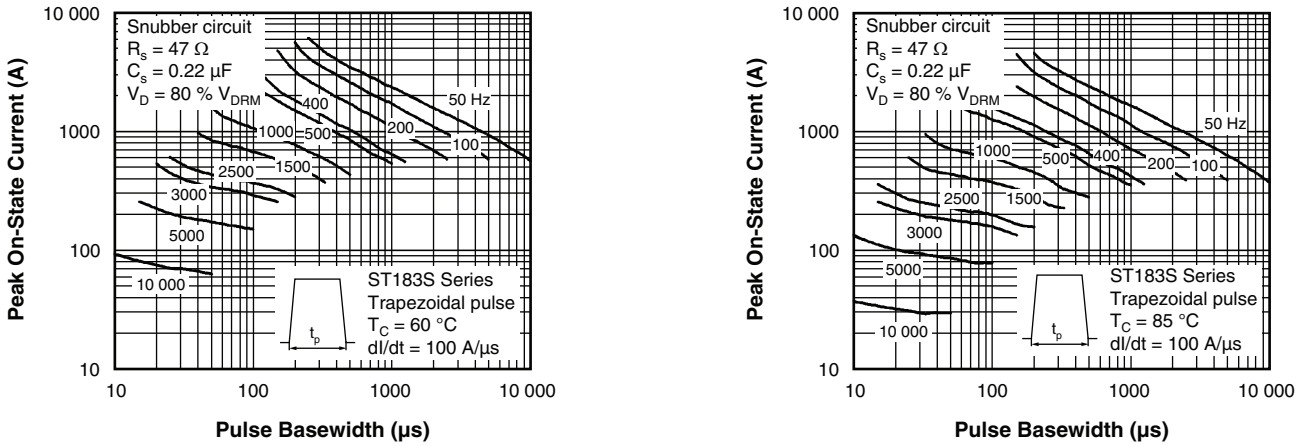


Fig. 13 - Frequency Characteristics

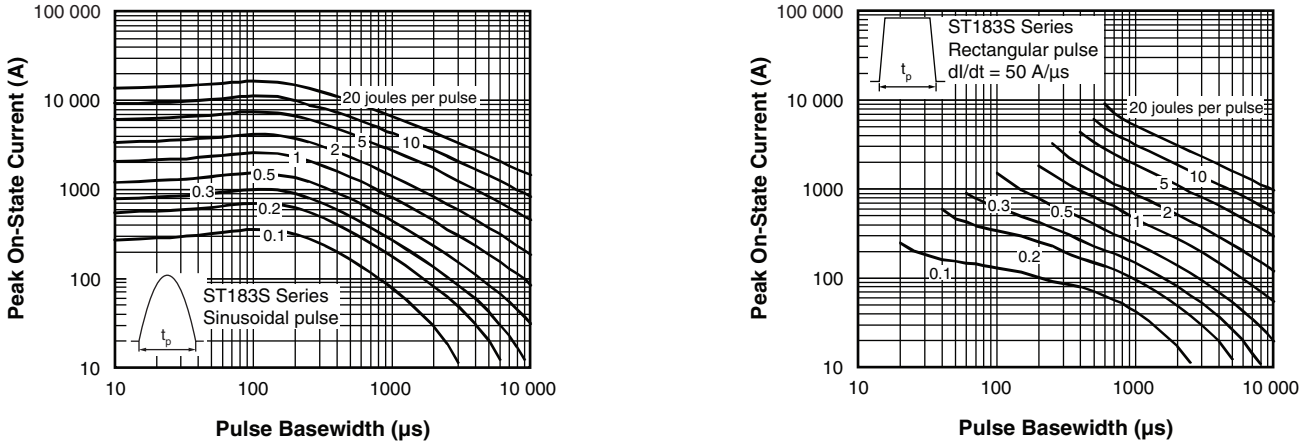


Fig. 14 - Maximum On-State Energy Power Loss Characteristics

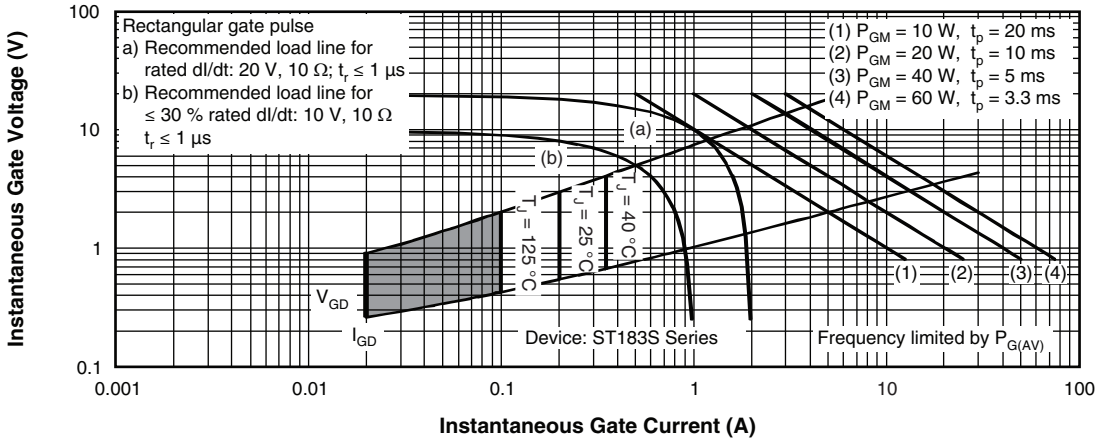


Fig. 15 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

VS-	ST	18	3	S	08	P	F	K	0	P
1	2	3	4	5	6	7	8	9	10	11

- 1 - Vishay Semiconductors product
- 2 - Thyristor
- 3 - Essential part number
- 4 - 3 = Fast turn-off
- 5 - S = Compression bonding stud
- 6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7 - P = Stud base 3/4" 16UNF-2A
- 8 - Reapplied dV/dt code (for t_q test condition)
- 9 - t_q code
- 10 - 0 = Eyelet terminals (gate and auxiliary cathode leads)
  1 = Fast-on terminals (gate and auxiliary cathode leads)
- 11 - None = standard production
  - P = Lead (Pb)-free

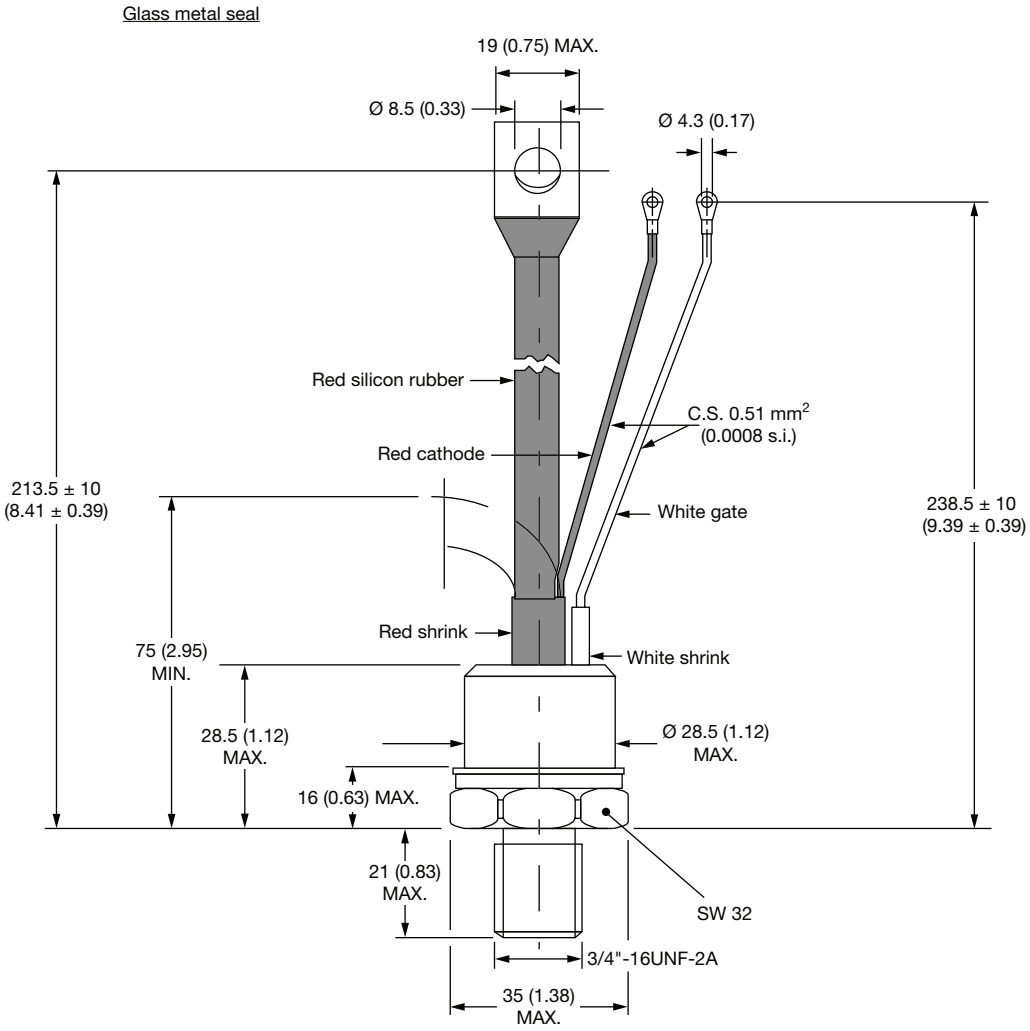
Note: For metric device M16 x 1.5 contact factory

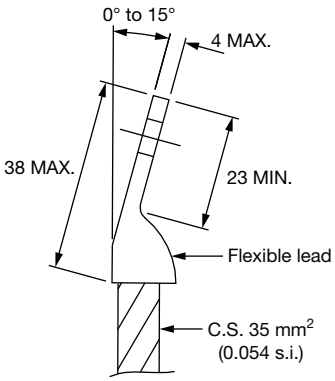
dV/dt - t_q combinations available		
dV/dt (V/µs)		200
t_q (µs)	15	FL
	20	FK

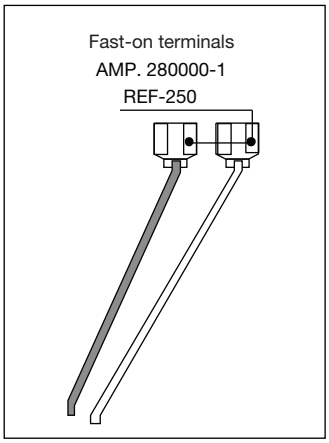
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95077

TO-209AB (TO-93)

DIMENSIONS in millimeters (inches)







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